

## Silicon PNP Power Transistors

## 2SA1227 2SA1227A

## DESCRIPTION

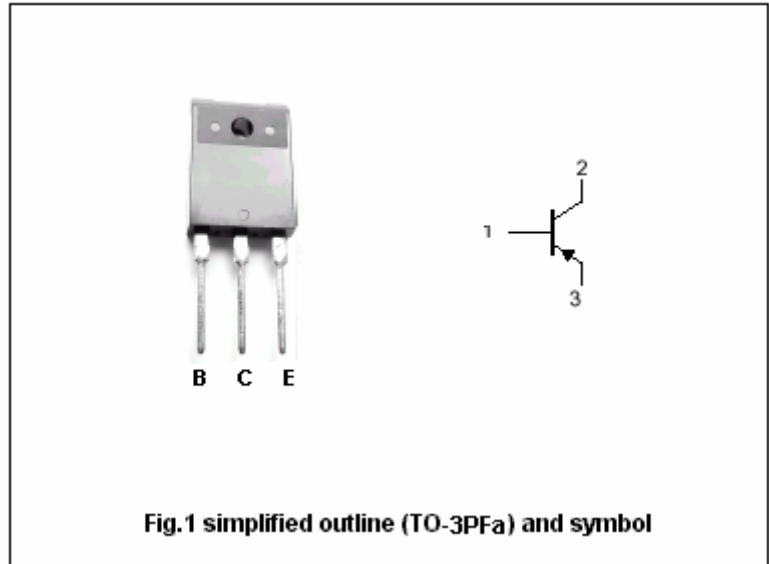
- With TO-3PFa package
- Complement to type 2SC2987/2987A
- High power dissipation

## APPLICATIONS

- For use in audio frequency power amplifier applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	2SA1227	-140	V
		2SA1227A	-160	
$V_{CEO}$	Collector-emitter voltage	2SA1227	-140	V
		2SA1227A	-160	
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-12	A
$I_{CM}$	Collector current-peak		-20	A
$P_T$	Total power dissipation	$T_C=25^\circ\text{C}$	120	W
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-5A ; I <sub>B</sub> =-0.5A		-0.8	-1.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-5A ; I <sub>B</sub> =-0.5A		-1.5	-2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-140V; I <sub>E</sub> =0			-50	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-3V; I <sub>C</sub> =0			-50	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-2A ; V <sub>CE</sub> =-5V	60		320	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-5A ; V <sub>CE</sub> =-5V	40			
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V; f=1MHz		280		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V		60		MHz

◆ h<sub>FE-1</sub> classifications

R	Q	P
60-120	100-200	160-320

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PACKAGE OUTLINE



Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.30\text{mm}$ )